

NCE N-Channel Enhancement Mode Power MOSFET

Description

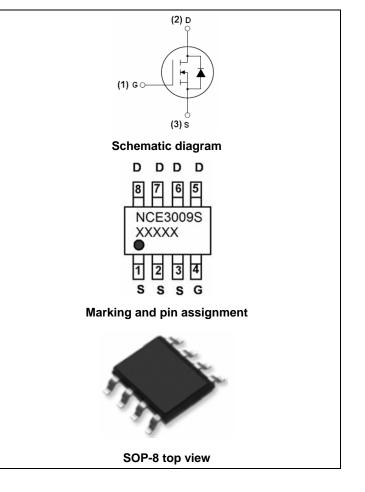
The NCE3009S uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =30V,I_D =9A
 R_{DS(ON)} < 9mΩ @ V_{GS}=10V
 R_{DS(ON)} <15mΩ @ V_{GS}=4.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- Power switching application
- Hard Switched and High Frequency Circuits
- Uninterruptible Power Supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE3009S	NCE3009S	SOP-8	Ø330mm	12mm	4000 units

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	9	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	6.4	А
Pulsed Drain Current	I _{DM}	60	А
Maximum Power Dissipation	PD	2.5	W
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{ extsf{ heta}JC}$	50	°C /W



Electrical Characteristics (T_A=25 $^\circ\!\!\mathrm{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	33	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} =30V, V_{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.5	2.2	V	
Drain Source On State Desistance		V_{GS} =10V, I _D =9A	-	7.6	9		
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =4.5V, I _D =9A	-	11.5	15	mΩ	
Forward Transconductance	g fs	V _{DS} =5V,I _D =9A	15	-	-	S	
Dynamic Characteristics (Note4)	I I		•				
Input Capacitance	C _{lss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	1210	-	PF	
Output Capacitance	C _{oss}		-	160	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	105	-	PF	
Switching Characteristics (Note 4)	<u> </u>		•				
Turn-on Delay Time	t _{d(on)}		-	5	-	nS	
Turn-on Rise Time	tr	V_{DD} =15V,I _D =9A	-	12	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =6 Ω	-	19	-	nS	
Turn-Off Fall Time	t _f		-	6	-	nS	
Total Gate Charge	Qg)/ -15)// -04	-	17.5	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =9A, V _{GS} =4.5V	-	3	-	nC	
Gate-Drain Charge	Q _{gd}	VGS-4.3V	-	4.1	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =9A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	9	А	

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

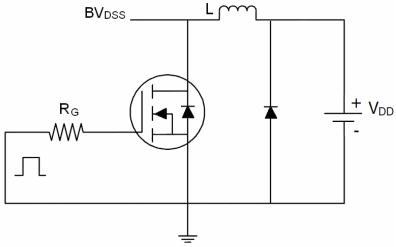
4. Guaranteed by design, not subject to production

5. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)=}150° C. The SOA curve provides a single pulse rating.

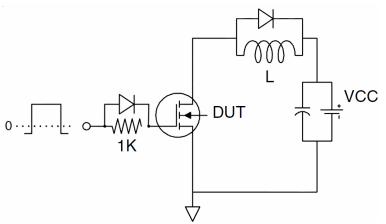


Test Circuit

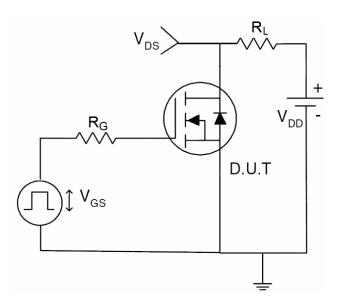
1) E_{AS} Test Circuits



2) Gate Charge Test Circuit:

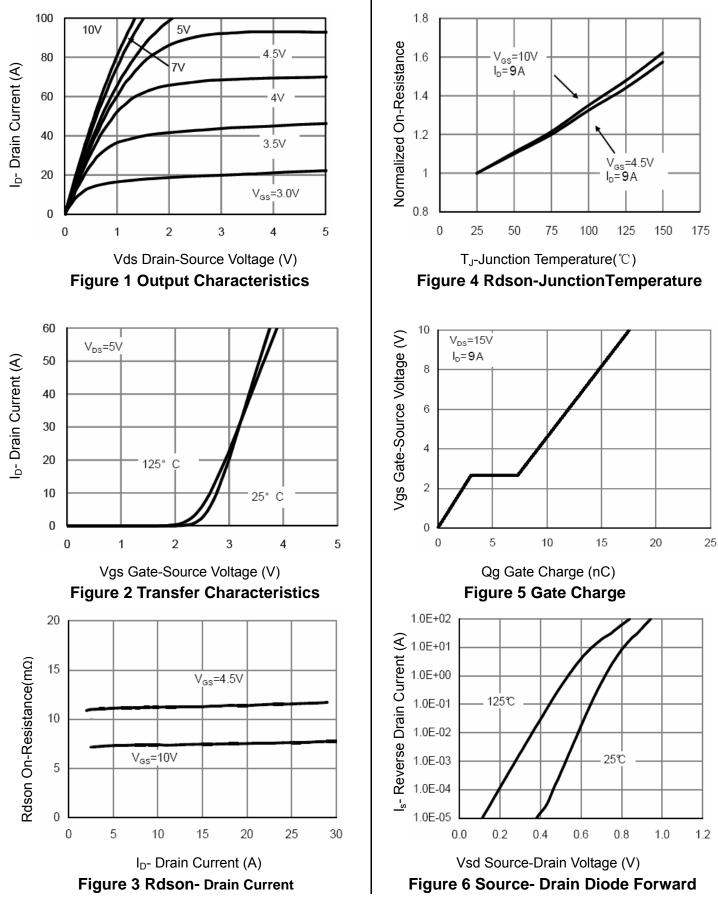


3) Switch Time Test Circuit:



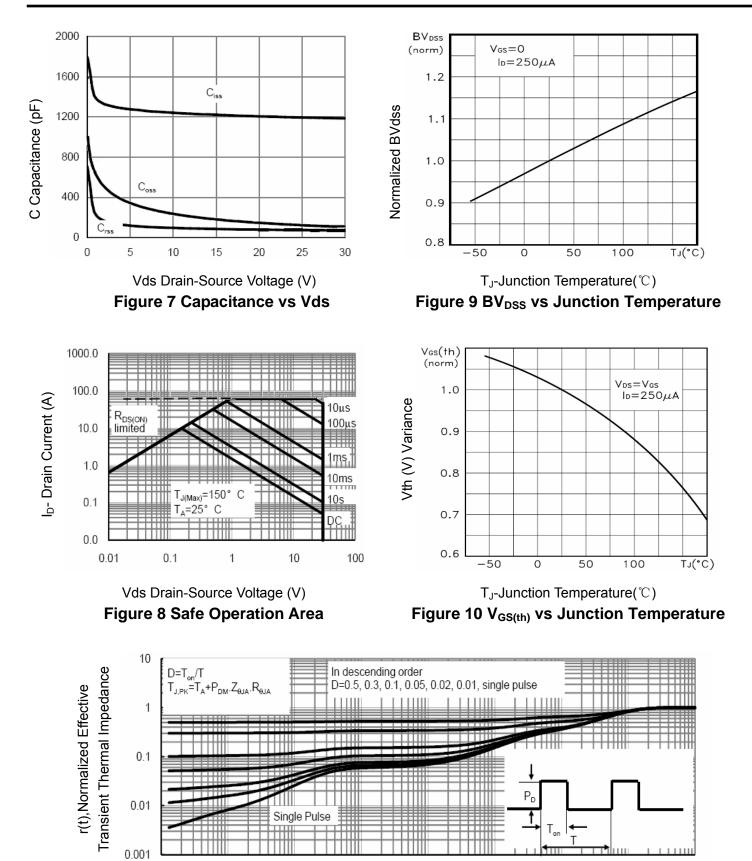


Typical Electrical and Thermal Characteristics (Curves)





http://www.ncepower.com



Square Wave Pluse Duration(sec)

0.1

1

10

100

Figure 11 Normalized Maximum Transient Thermal Impedance

0.00001

0.0001

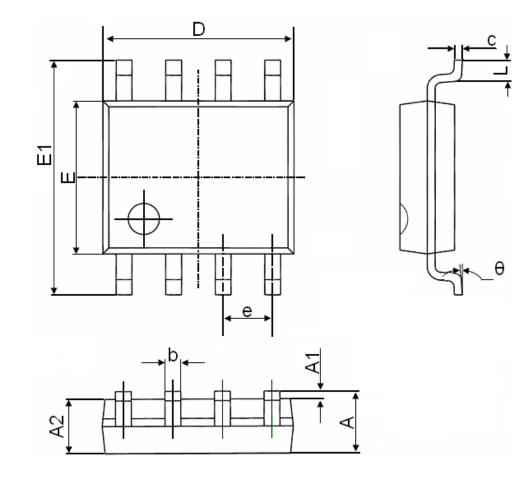
0.001

0.01

1000



SOP-8 Package Information



Symbol	Dimensions	n Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
e	1.270	(BSC)	0.050(BSC)		
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	



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